NPN EPITAXIAL SILICON TRANSISTORS WMBTA42

High Voltage Transistor

Die Size 0.6*0.6mm

SOT—23

GUARANTEED PROBED CHARACTERISTICS (T_A=25℃)

Characteristic	Symbol	Test Conditions	Limits			Units
			Min	Typ	Max	
Collector-emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA	300	-	-	V
Collector-Base Breakdown Voltage	V_{CBO}	I_C=100uA				
Collector Cut-off Current	I_{CBO}	V_{CB}=260V	-	-	100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=6V	-	-	100	nA
DC Current Gain	h_{FE}	V_{CE}=10V, I_C=1mA V_{CE}=10V, I_C=10mA V_{CE}=10V, I_C=30mA	30 40 40	-	-	
Base-Emitter Saturation Voltage	V_{BEsat}	I_C=20mA, I_b=2mA	-	-		V
Collector-Emitter Saturation Voltage	V_{CEsat}	I_C=20mA, I_B=2mA	-	-		
Transition Frequency	f_r	V_{CE}=20V, I_C=10mA,f=10MHz	50	-	-	MHz
Collector-Base Capacitance	C_{cb}	V_{CB}=20V, f=1MHz	-	-	3.0	pF

NOTES: Due to probe testing limitations, only the DC parameters are tested.